



## Description

The STN484D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



**TO-252-2L**

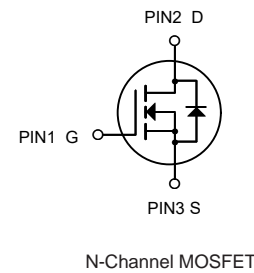
## General Features

$V_{DS} = 30V$   $I_D = 50 A$

$R_{DS(ON)} < 10m\Omega @ V_{GS}=10V$

## Application

- Battery protection
- Load switch
- Uninterruptible power supply



## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
STN484D	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	112	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	24.2	mJ
$I_{AS}$	Avalanche Current	22	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	37.5	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	4	$^\circ C/W$



**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.0193	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	7.5	10	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	11	18	
V <sub>GS(th)</sub>	Gate Threshold Voltage		1.2	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	---	-3.97	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =30A	---	34	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.8	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)		---	9.8	---	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	4.2	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.6	---	
T <sub>d(on)</sub>	Turn-On Delay Time		---	4	---	ns
T <sub>r</sub>	Rise Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3	---	8	---	
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =15A	---	31	---	
T <sub>f</sub>	Fall Time		---	4	---	
C <sub>iss</sub>	Input Capacitance		---	940	---	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	131	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	109	---	
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>		---	---	43	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	112	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =30A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	8.5	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	2.2	---	nC

Note :

- 1 .The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3 .The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=22A
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



### Typical Characteristics

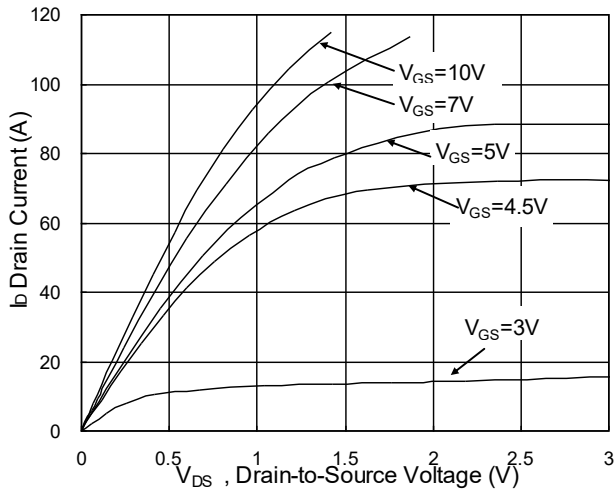


Fig.1 Typical Output Characteristics

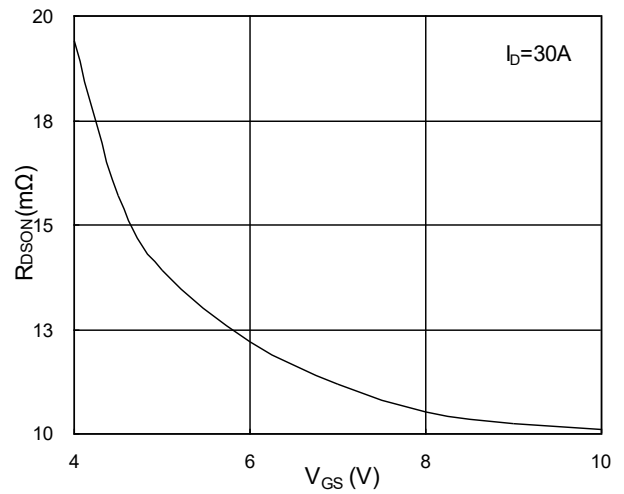


Fig.2 On-Resistance vs. G-S Voltage

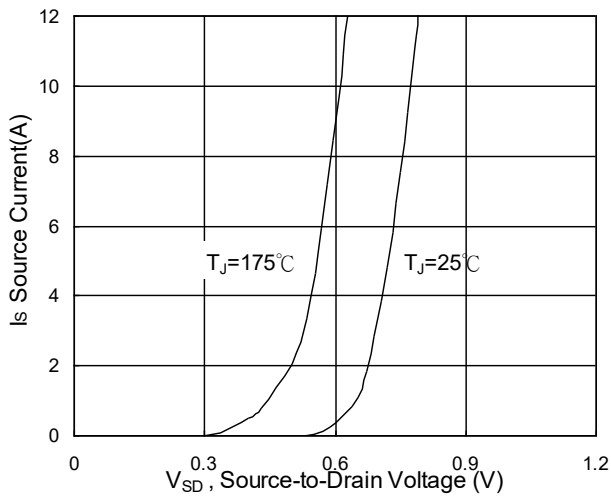


Fig.3 Forward Characteristics of Reverse

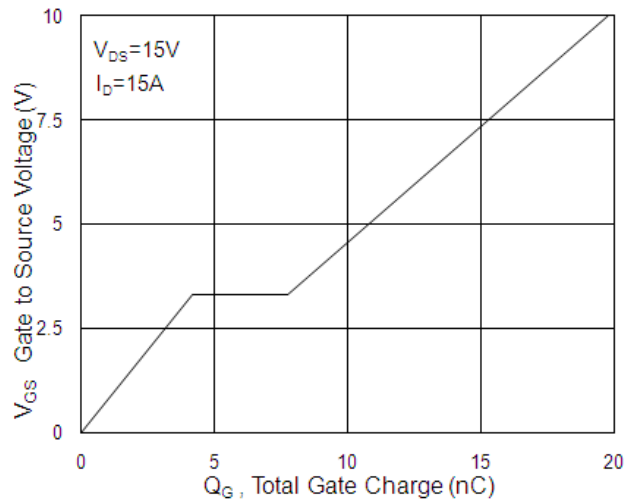


Fig.4 Gate-Charge Characteristics

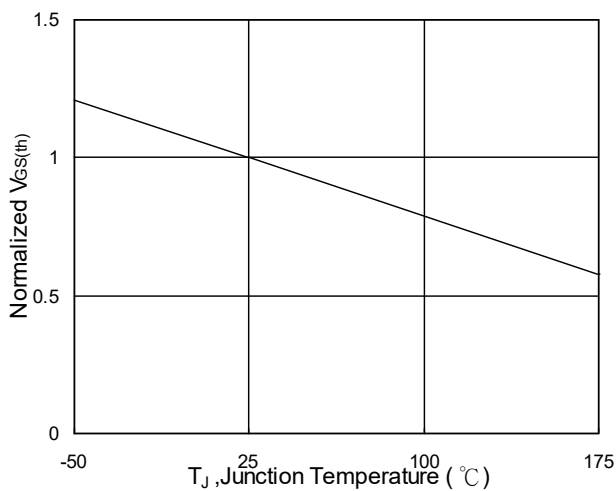


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

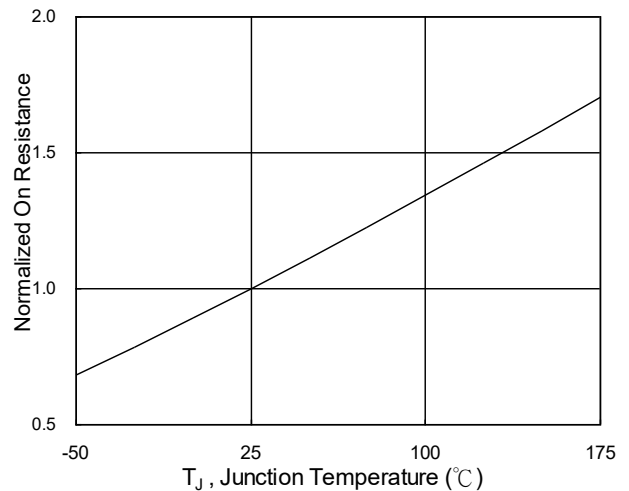


Fig.6 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>

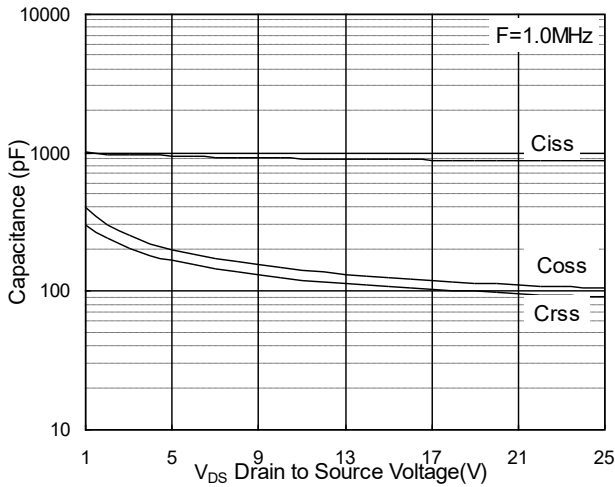


Fig.7 Capacitance

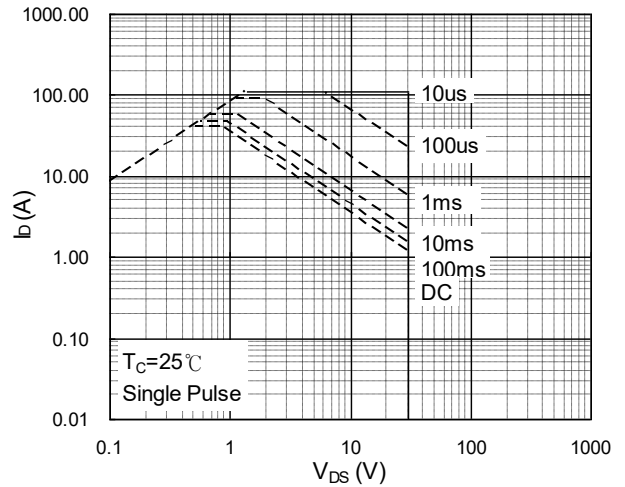


Fig.8 Safe Operating Area

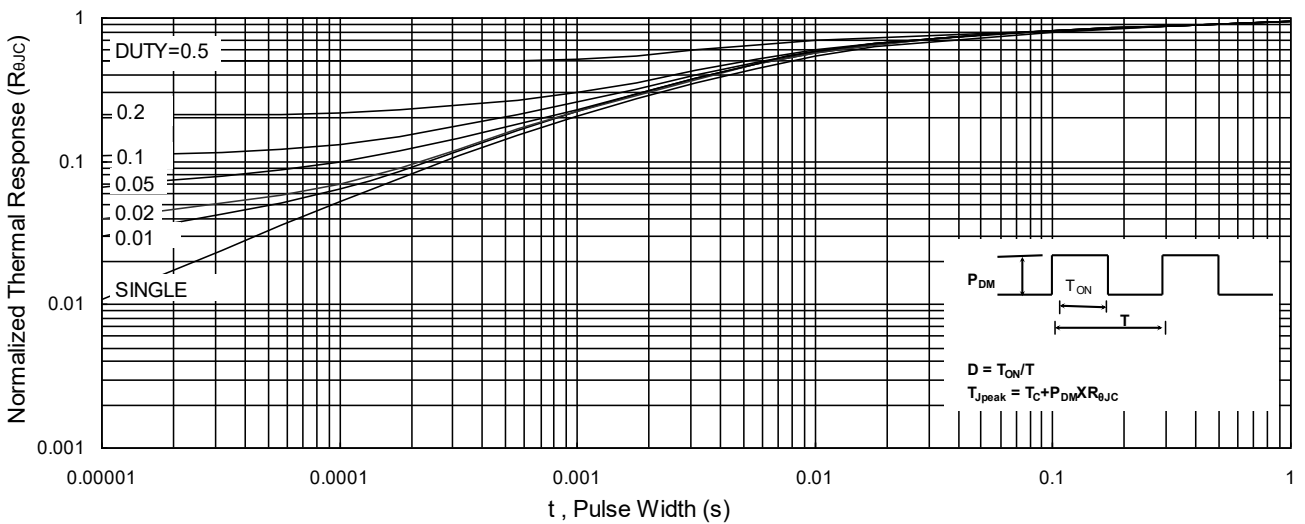


Fig.9 Normalized Maximum Transient Thermal Impedance

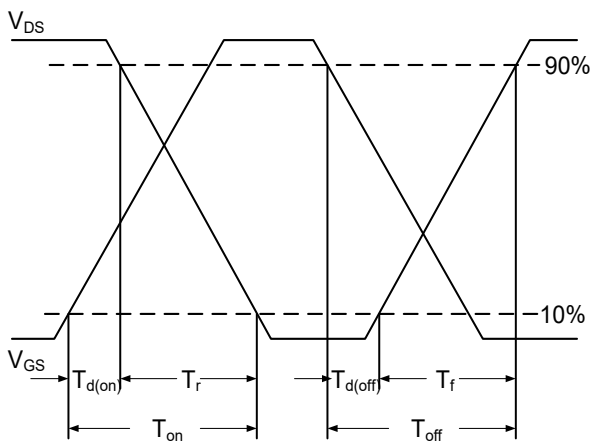


Fig.10 Switching Time Waveform

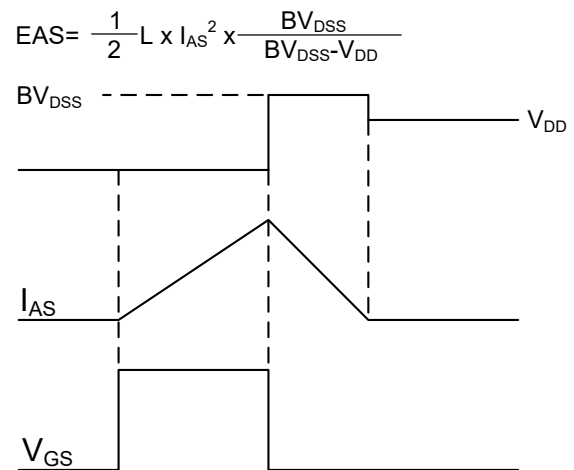
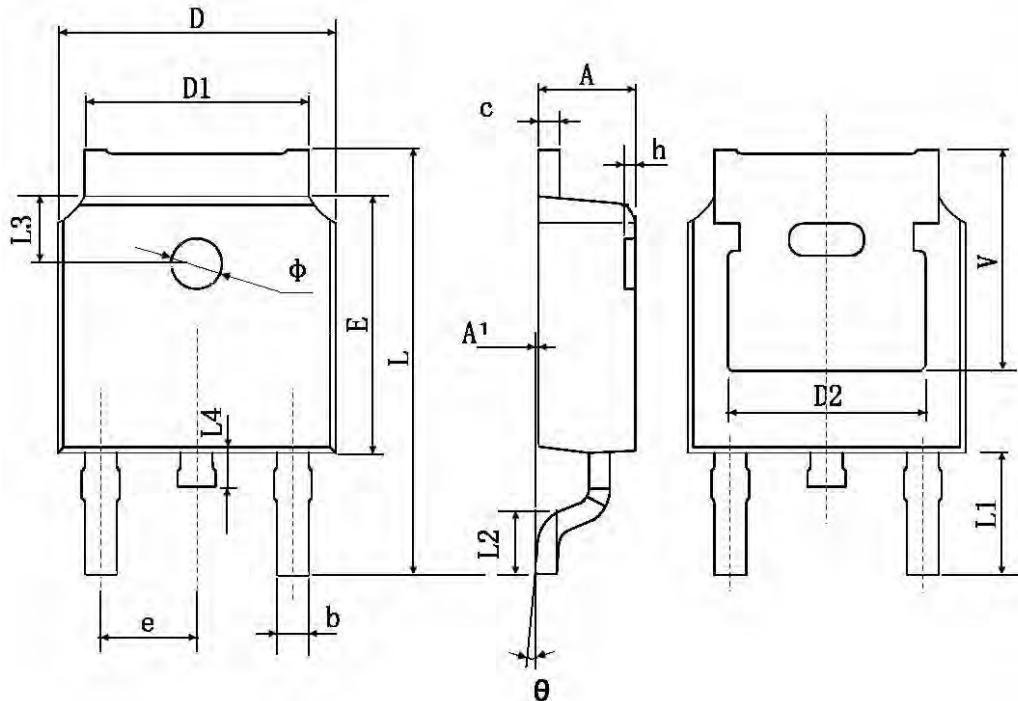


Fig.11 Unclamped Inductive Switching Waveform



### TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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